

**In the drawings:**

New Fig. 7A is added. Fig. 7A illustrates matter which was originally disclosed in the specification as filed. (“A silicide can be formed in the remaining polysilicon material at this step to further reduce gate resistance, for example, by refractory metal deposition and silicide formation.”) Page 11, Line 27 through Page 12, Line 1 of original disclosure as filed. The Applicant includes a “NEW SHEET” for Fig. 7A. No new matter is added.

New Fig. 13A is added. Fig. 13A also illustrates matter which was originally disclosed in the specification as filed. (“Frontside metal is deposited and patterned to delineate the gate and source (cathode) electrodes.”) Page 5, Lines 10-11 of original disclosure as filed. (“The completion steps also include opening gate contact vias at discrete locations, which can be done in this process without critical alignment, and passivating the surface.”) Page 14, Lines 25-28 of original disclosure as filed. The Applicant includes a “NEW SHEET” for Fig. 13A. No new matter is added.

The Applicant resubmits Fig. 6B and 6C with the requested marking “REPLACEMENT SHEET.” Resubmitted Fig. 6B and 6C match those which were submitted with the previous response. Annotated sheets for Fig. 6B and 6C were also provided in the previous response.